

# SOLAR

## InOxSide<sup>+</sup>

R|E|N|A|.



## Inline junction isolation and rear side polishing

The InOxSide<sup>+</sup> combines junction isolation and rear side polishing as a perfect preparation for a superior surface passivation. The patented single side etching technology ensures powerful polishing already at low etch depths with lowest cost of ownership. Furthermore, the PreCon and RaPID features offer further flexible configurations for most advanced cell concepts and PID-free cells.

### Areas of application

- Rear side polishing for high efficiency solar cells, e.g. PERC and PERT
- Junction isolation and PSG-removal
- Designed for multi- and monocrystalline wafers
- Wafer transfer systems available for automatic loading and unloading

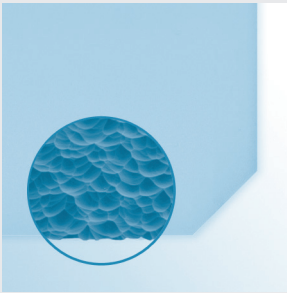
### Features and benefits

- Inline single side processing
- Patented process:
  - High quality smoothing
  - Low CoO
- Suited for all relevant passivation layers including AlOx
- Straight line footprint
- Suitable for both multi- and monocrystalline cells

### Options

- PreCon: advanced rear side polishing. The additional PreCon module offers a boost in etch depth to more than 6  $\mu\text{m}$  for most demanding cell concepts and highest efficiencies.
- RaPID: For PID-free cells. The RaPID module forms a thin oxide on the wafer surface prior to AR deposition - a key factor for the production of PID-free cells. Integrated within the InOxSide<sup>®</sup> tool, the RaPID module does not increase the equipment footprint.





Smooth  
rear side

RENA



Front view InOxSide+

## Technical Data InOxSide+

Platform	RENA NIAK2 (5 lanes)
Process	Junction isolation, rear side polishing and PSG removal
Dimensions	8400 x 2150 x 2350 mm (length x width x height)
Throughput	up to 5000 wafer/h (gross)
Wafer thickness	> 150 $\mu\text{m}$
Wafer size	156-166 mm, square and pseudo-square
Etch depth	1 - 5 $\mu\text{m}$ , higher etch-off on request

RENA V50002